



MDL-III-830R/1~500mW

INFRARED DIODE LASER AT 830nm




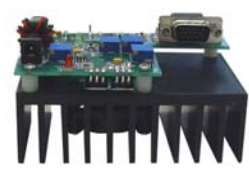
Diode infrared laser module at 830nm is made features of ultra compact, long lifetime, low cost and easy operating, which is used in measurement, communication, spectrum analysis, etc.



SPECIFICATIONS

Wavelength (nm)	830 ± 5		
Output power (mW)	>1, 50, 100, ... , 500		
Energy distribution	Even		
Beam Spot	Round		
Power stability (rms, over 4 hours)	<1%, <3%, <5%		
Warm-up time (minutes)	<5		
Beam divergence, full angle (mrad)	<8.0		
Dimensions of beam at the aperture (mm)	~2.0		
Beam height from base plate (mm)	24.8		
Pointing stability after warm-up (mrad)	<0.05		
Operating temperature (°C)	10~35		
Power supply (90-264VAC or 5VDC)	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
TTL / Analog modulation	Optional, 2kHz or higher (on request, up to 30kHz)		
Expected lifetime (hours)	10000		
Warranty	1 year		



MxL-III-830R	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
 <p style="text-align: center;">140. 8(L)×73(W)×46. 2(H) mm³, 0.6kg</p>	 <p style="text-align: center;">154 (L) ×155(W) ×95 (H) mm³, 1.5kg</p>	 <p style="text-align: center;">133 (L) ×130(W) ×65 (H) mm³, 1.2kg</p>	 <p style="text-align: center;">100 (L) ×60(W) ×56 (H) mm³, 0.2kg</p>
